VS-HFA04TB60S-M3

Vishay Semiconductors

HEXFRED[®], Ultrafast Soft Recovery Diode, 4 A



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PRIMARY CHARACTERISTICS						
I _{F(AV)} 4 A						
V _R	600 V					
V _F at I _F	1.4 V					
t _{rr} (typ.)	17 ns					
T _J max.	150 °C					
Package	D ² PAK (TO-263AB)					
Circuit configuration	Single					

FEATURES

- Ultrafast recovery
- Ultrasoft recovery
- Very low I_{RRM}
- Very low Q_{rr}
- Specified at operating temperature
- Meets MSL level 1, per J-STD-020, LF maximum peak of 245 °C
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

BENEFITS

- Reduced RFI and EMI
- Reduced power loss in diode and switching transistor
- Higher frequency operation
- Reduced snubbing
- · Reduced parts count

DESCRIPTION

VS-HFA04TB60S is a state of the art ultrafast recovery diode. Employing the latest in epitaxial construction and advanced processing techniques it features a superb combination of characteristics which result in performance which is unsurpassed by any rectifier previously available. With basic ratings of 600 V and 4 A continuous current, the VS-HFA04TB60S is especially well suited for use as the companion diode for IGBTs and MOSFETs. In addition to ultrafast recovery time, the HEXFRED® product line features extremely low values of peak recovery current (I_{RBM}) and does not exhibit any tendency to "snap-off" during the tb portion of recovery. The HEXFRED features combine to offer designers a rectifier with lower noise and significantly lower switching losses in both the diode and the switching transistor. These HEXFRED advantages can help to significantly reduce snubbing, component count and heatsink sizes. The HEXFRED VS-HFA04TB60S is ideally suited for applications in power supplies and power conversion systems (such as inverters), motor drives, and many other similar applications where high speed, high efficiency is needed.

ABSOLUTE MAXIMUM RATINGS							
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS			
Cathode to anode voltage	V _R		600	V			
Maximum continuous forward current	I _F	T _C = 100 °C	4				
Single pulse forward current	I _{FSM}		25	А			
Maximum repetitive forward current	I _{FRM}		16				
Maximum power dissipation	PD	T _C = 25 °C	25	W			
Maximum power dissipation		T _C = 100 °C	10	vv			
Operating junction and storage temperature range	T _J , T _{Stg}		-55 to +150	°C			

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ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)								
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS	
Cathode to anode breakdown voltage	V_{BR}	I _R = 100 μA		600	-	-		
		I _F = 4.0 A	See fig. 1	-	1.5	1.8	v	
Maximum forward voltage	V _{FM}	I _F = 8.0 A		-	1.8	2.2		
		I _F = 4.0 A, T _J = 125 °C		-	1.4	1.7		
Maximum reverse leakage current	1	$V_R = V_R$ rated	See fig. 2	-	0.17	3.0		
Maximum reverse leakage current	I _{RM}	$T_J = 125 \text{ °C}, V_R = 0.8 \text{ x } V_R \text{ rated}$	See fig. 2	-	44	300	μA	
Junction capacitance	CT	V _R = 200 V	See fig. 3	-	4.0	8.0	pF	
Series inductance	L _S	Measured lead to lead 5 mm from package body -		8.0	-	nH		

DYNAMIC RECOVERY CHARACTERISTICS (T _J = 25 °C unless otherwise specified)								
PARAMETER	SYMBOL	TEST CON	IDITIONS	MIN.	TYP.	MAX.	UNITS	
	t _{rr}	$I_F = 1.0 \text{ A}, \text{ d}I_F/\text{d}t = 200 \text{ A}$	õs, V _R = 30 V	-	17	-		
Reverse recovery time See fig. 5, 6	t _{rr1}	T _J = 25 °C		-	28	42	ns	
	t _{rr2}	T _J = 125 °C	I _F = 4.0 A di _F /dt = 200 A/μs	-	38	57	T I	
Peak recovery current	I _{RRM1}	T _J = 25 °C		-	2.9	5.2	A	
Feat recovery current	I _{RRM2}	T _J = 125 °C		-	3.7	6.7	~	
Reverse recovery charge	Q _{rr1}	T _J = 25 °C	$V_{\rm B} = 200 \text{ V}$	-	40	60	nC	
See fig. 7	Q _{rr2}	T _J = 125 °C		-	70	105	110	
Peak rate of fall of recovery current	di _{(rec)M} /dt1	T _J = 25 °C		-	280	-	A∕µs	
during t _b , see fig. 8	di _{(rec)M} /dt2	T _J = 125 °C		-	235	-	γvµs	

THERMAL - MECHANICAL SPECIFICATIONS								
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS		
Lead temperature	T _{lead}	0.063" from case (1.6 mm) for 10 s	-	-	300	°C		
Thermal resistance, junction-to-case	R _{thJC}		-	-	5.0	K/W		
Thermal resistance, junction-to-ambient	R _{thJA}	Typical socket mount	-	-	80	r\/ vv		
Woisht			-	2.0	-	g		
Weight			-	0.07	-	oz.		
Marking device		Case style D ² PAK (TO-263AB)		HFA04	TB60S			



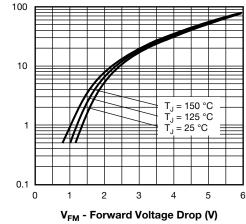


Fig. 1 - Maximum Forward Voltage Drop vs. Instantaneous Forward Current

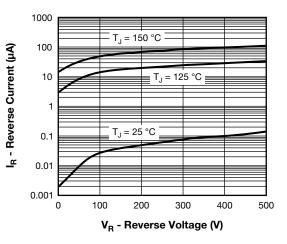


Fig. 2 - Typical Reverse Current vs. Reverse Voltage

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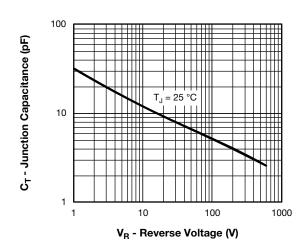


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

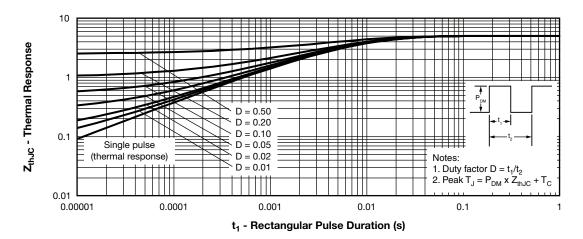


Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics

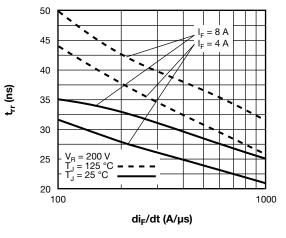


Fig. 5 - Typical Reverse Recovery Time vs. $di_{\mbox{\scriptsize F}}/dt$

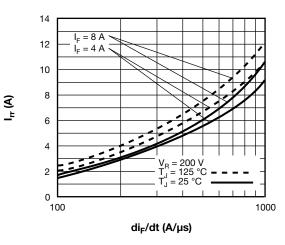


Fig. 6 - Typical Recovery Current vs. di_F/dt

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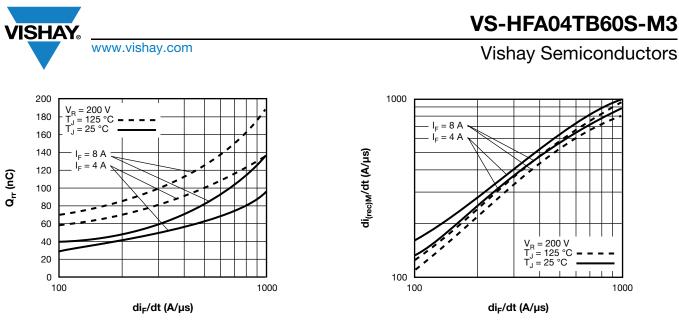


Fig. 7 - Typical Stored Charge vs. di_F/dt



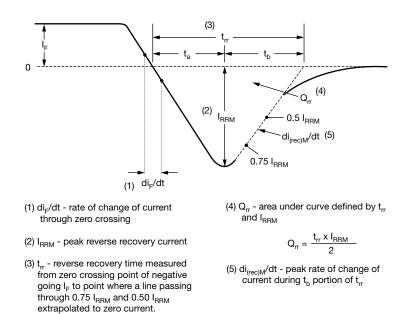


Fig. 9 - Reverse Recovery Waveform and Definitions

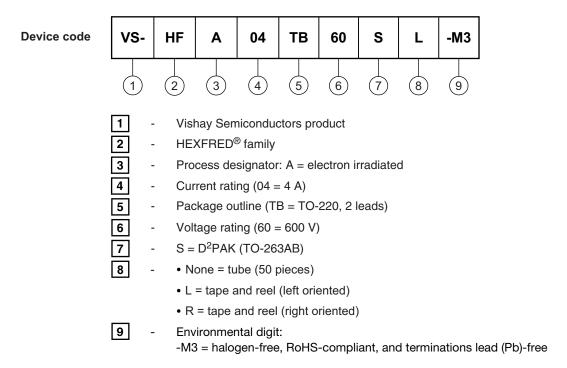
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ORDERING INFORMATION TABLE

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ORDERING INFORMATION (Example)							
PREFERRED P/N BASE QUANTITY PACKAGING DESCRIPTION							
VS-HFA04TB60S-M3	50	Antistatic plastic tube					
VS-HFA04TB60SL-M3	800	13" diameter reel					
VS-HFA04TB60SR-M3	800	13" diameter reel					

LINKS TO RELATED DOCUMENTS					
Dimensions www.vishay.com/doc?96164					
Part marking information	www.vishay.com/doc?95444				
Packaging information	www.vishay.com/doc?96424				

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D²PAK

DIMENSIONS in millimeters and inches



ota	ted	90	°C
<u>S</u>	cale	<u>ə:</u> 8	:1

SYMBOL	MILLIM	ETERS	INCHES		NOTES	
STMBOL	MIN.	MAX.	MIN.	MAX.	NOTES	
А	4.06	4.83	0.160	0.190		
A1	0.00	0.254	0.000	0.010		
b	0.51	0.99	0.020	0.039		
b1	0.51	0.89	0.020	0.035	4	
b2	1.14	1.78	0.045	0.070		
b3	1.14	1.73	0.045	0.068	4	
с	0.38	0.74	0.015	0.029		
c1	0.38	0.58	0.015	0.023	4	
c2	1.14	1.65	0.045	0.065		
D	8.51	9.65	0.335	0.380	2	

SYMBOL		MILLIM	ETERS	INCHES		NOTES
	STNDUL	MIN.	MAX.	MIN.	MAX.	NOTES
	D1	6.86	8.00	0.270	0.315	3
	E	9.65	10.67	0.380	0.420	2, 3
	E1	7.90	8.80	0.311	0.346	3
	е	2.54 BSC		0.100 BSC		
	Н	14.61	15.88	0.575	0.625	
	L	1.78	2.79	0.070	0.110	
	L1	-	1.65	-	0.066	3
	L2	1.27	1.78	0.050	0.070	
	L3	0.25 BSC		0.010	BSC	
	L4	4.78	5.28	0.188	0.208	

Notes

⁽¹⁾ Dimensioning and tolerancing per ASME Y14.5 M-1994

(2) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body

(3) Thermal pad contour optional within dimension E, L1, D1 and E1

⁽⁴⁾ Dimension b1 and c1 apply to base metal only

(5) Datum A and B to be determined at datum plane H

(6) Controlling dimension: inches

⁽⁷⁾ Outline conforms to JEDEC[®] outline TO-263AB

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